

Please amend the above identified application as follows.

In the Claims:

- 1 1. (twice amended) A semiconductor light-emitting device  
2 comprising:  
3 a substrate;  
4 an n-type lower electrode provided on a back surface  
5 of said substrate;  
6 a light-emitting layer provided on said substrate;  
7 a p-type semiconductor layer provided on said  
8 light-emitting layer;  
9 an Au thin film provided on said p-type semiconductor  
10 layer and having a thickness of 1 nm to 3 nm; and  
11 an n-type transparent conductive film provided on said  
12 Au thin film, with said Au thin film between said p-type  
13 semiconductor layer and said n-type transparent conductive  
14 film, wherein said n-type transparent conductive film is  
15 formed by laser ablation and has properties as result from  
16 the laser ablation.

Claims 2 and 3 have previously been cancelled.

Claims 4 and 5 remain as previously amended.

Claim 6 is maintained unchanged.

Please cancel claim 7.

Claims 8 to 15 have previously been cancelled.